

Description

The SX80N08D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 80V$ $I_D = 80A$

$R_{DS(ON)} < 6.5m\Omega$ $V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply

**Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)**

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	80	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_c=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	80	A
$I_D @ T_c=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	42.5	A
IDM	Pulsed Drain Current ²	170	A
EAS	Single Pulse Avalanche Energy ³	57.8	mJ
IAS	Avalanche Current	34	A
$P_D @ T_c=25^\circ C$	Total Power Dissipation ⁴	56	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	2.2	$^\circ C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$\text{V}_{\text{GS}}=0\text{V}$, $\text{I}_D=250\mu\text{A}$	80	---	---	V
$\text{R}_{\text{DS(ON)}}$	Static Drain-Source On-Resistance ²	$\text{V}_{\text{GS}}=10\text{V}$, $\text{I}_D=20\text{A}$	---	4.8	6.5	$\text{m}\Omega$
$\text{R}_{\text{DS(ON)}}$	Static Drain-Source On-Resistance ²	$\text{V}_{\text{GS}}=4.5\text{V}$, $\text{I}_D=20\text{A}$	---	6.3	8.5	$\text{m}\Omega$
$\text{V}_{\text{GS(th)}}$	Gate Threshold Voltage	$\text{V}_{\text{GS}}=\text{V}_{\text{DS}}$, $\text{I}_D=250\mu\text{A}$	1.0	---	2.5	V
I_{DSS}	Drain-Source Leakage Current	$\text{V}_{\text{DS}}=64\text{V}$, $\text{V}_{\text{GS}}=0\text{V}$, $T_J=25^\circ\text{C}$	---	---	1	uA
		$\text{V}_{\text{DS}}=64\text{V}$, $\text{V}_{\text{GS}}=0\text{V}$, $T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$\text{V}_{\text{GS}}=\pm 20\text{V}$, $\text{V}_{\text{DS}}=0\text{V}$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$\text{V}_{\text{DS}}=5\text{V}$, $\text{I}_D=20\text{A}$	---	75	---	S
R_{g}	Gate Resistance	$\text{V}_{\text{DS}}=0\text{V}$, $\text{V}_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	---	0.5	---	Ω
Q_{g}	Total Gate Charge (10V)	$\text{V}_{\text{DS}}=40\text{V}$, $\text{V}_{\text{GS}}=10\text{V}$, $\text{I}_D=20\text{A}$	---	40	---	nC
Q_{gs}	Gate-Source Charge		---	7.2	---	
Q_{gd}	Gate-Drain Charge		---	6.5	---	
$\text{T}_{\text{d(on)}}$	Turn-On Delay Time	$\text{V}_{\text{DD}}=40\text{V}$, $\text{V}_{\text{GS}}=10\text{V}$, $\text{R}_{\text{G}}=3\Omega$, $\text{I}_D=20\text{A}$	---	8.3	---	ns
T_{r}	Rise Time		---	4.2	---	
$\text{T}_{\text{d(off)}}$	Turn-Off Delay Time		---	36	---	
T_{f}	Fall Time		---	6.9	---	
C_{iss}	Input Capacitance	$\text{V}_{\text{DS}}=40\text{V}$, $\text{V}_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	---	2860	---	pF
C_{oss}	Output Capacitance		---	410	---	
C_{rss}	Reverse Transfer Capacitance		---	38	---	
I_{s}	Continuous Source Current ^{1,5}	$\text{V}_{\text{G}}=\text{V}_{\text{D}}=0\text{V}$, Force Current	---	---	48	A
V_{SD}	Diode Forward Voltage ²	$\text{V}_{\text{GS}}=0\text{V}$, $\text{I}_{\text{s}}=\text{A}$, $T_J=25^\circ\text{C}$	---	0.77	1.0	V
t_{rr}	Reverse Recovery Time	$\text{I}_{\text{F}}=20\text{A}$, $\frac{d\text{I}}{dt}=100\text{A}/\mu\text{s}$, $T_J=25^\circ\text{C}$	---	27	---	nS
Q_{rr}	Reverse Recovery Charge		---	89	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $\text{V}_{\text{DD}}=25\text{V}$, $\text{V}_{\text{GS}}=10\text{V}$, $\text{L}=0.1\text{mH}$, $\text{I}_{\text{AS}}=34\text{A}$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_{D} and I_{DM} , in real applications , should be limited by total power dissipation.
- 6.The maximum current rating is package limited.

Typical Characteristics

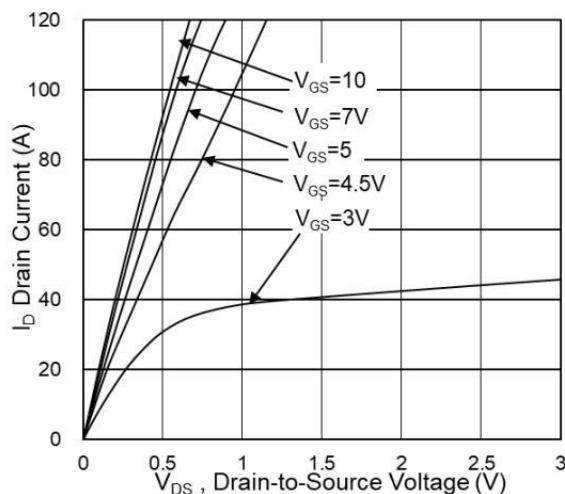


Fig.1 Typical Output Characteristics

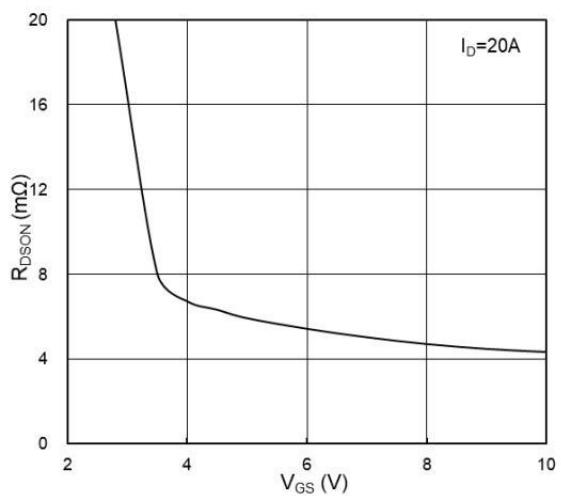


Fig.2 On-Resistance vs G-S Voltage

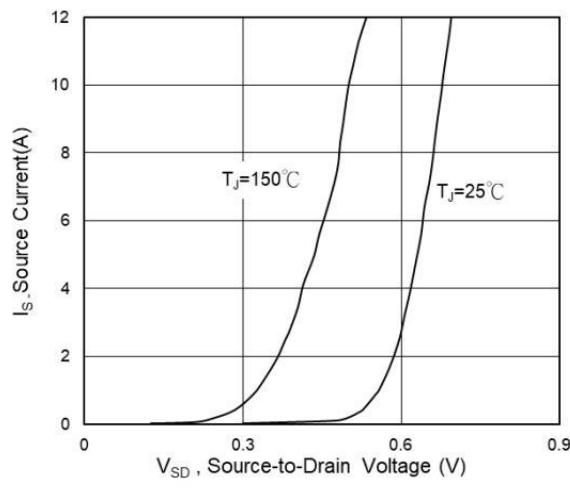


Fig.3 Source Drain Forward Characteristics

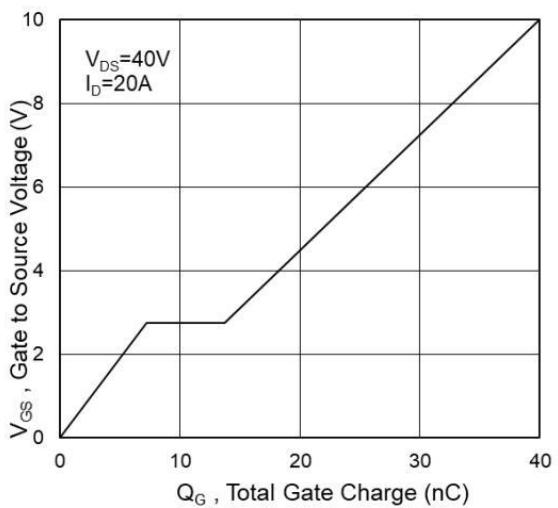


Fig.4 Gate-Charge Characteristics

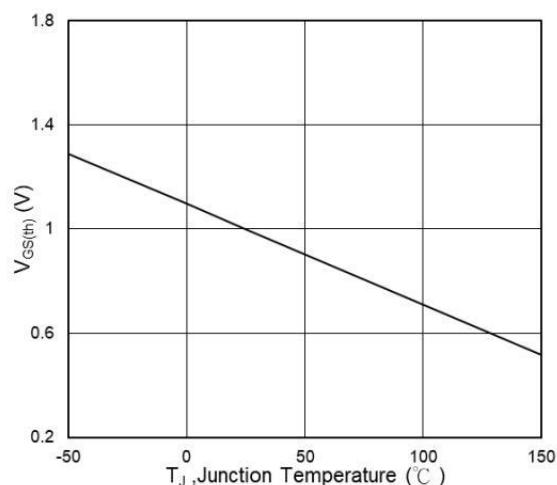


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

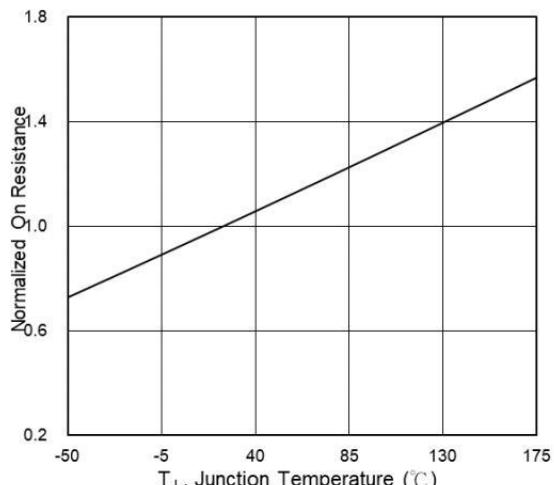


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

Typical Characteristics

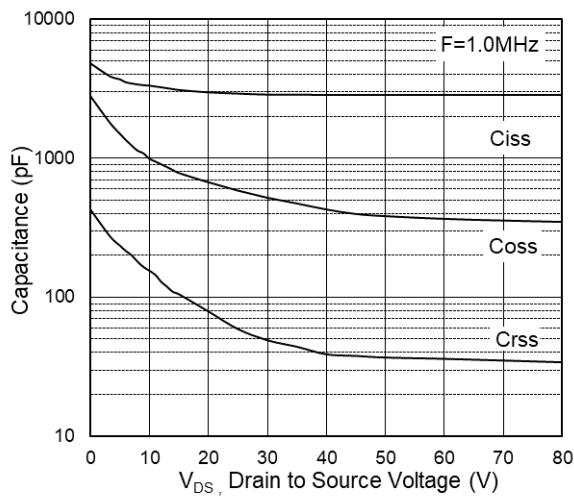


Fig.7 Capacitance

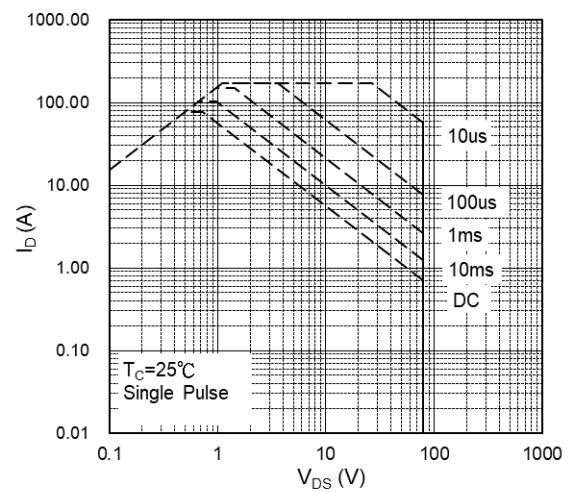


Fig.8 Safe Operating Area

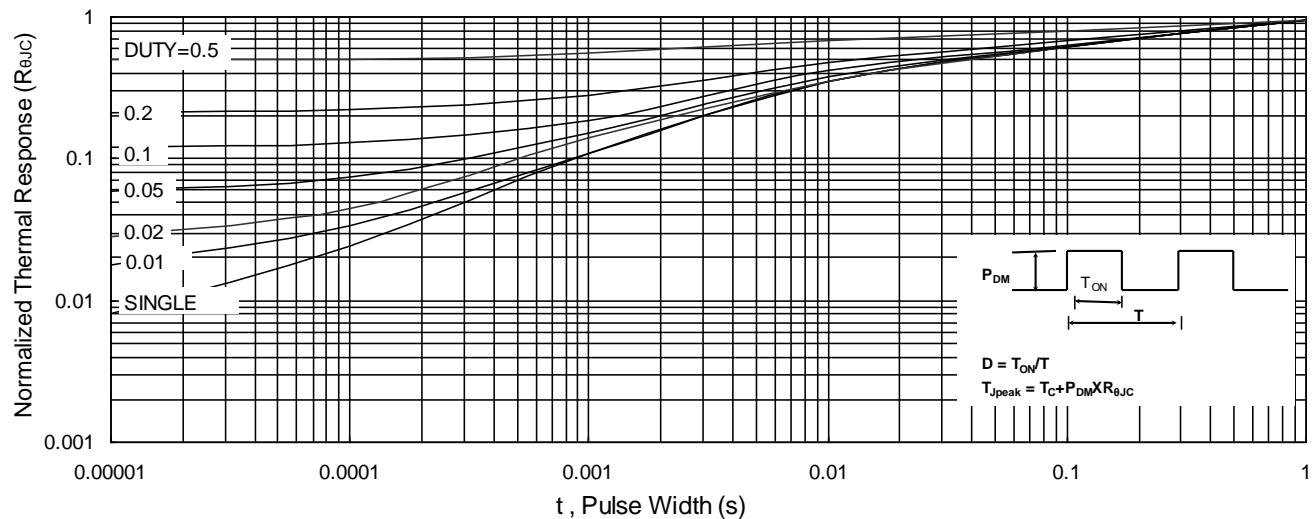


Fig.9 Normalized Maximum Transient Thermal Impedance

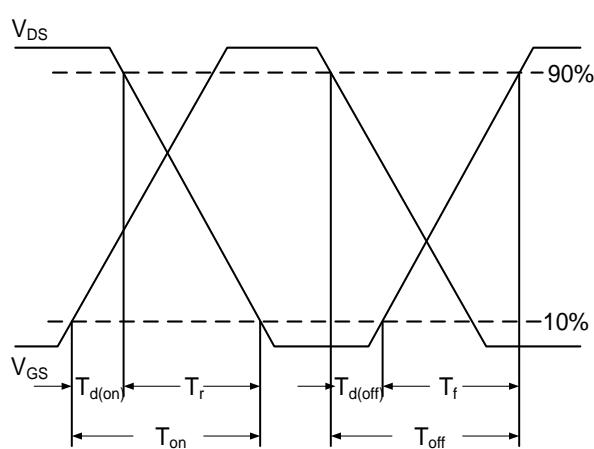


Fig.10 Switching Time Waveform

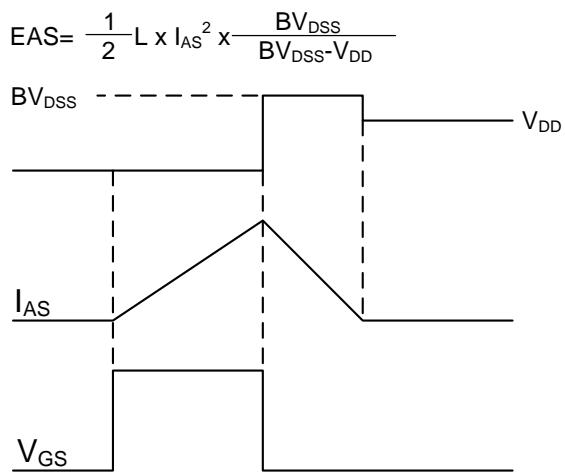
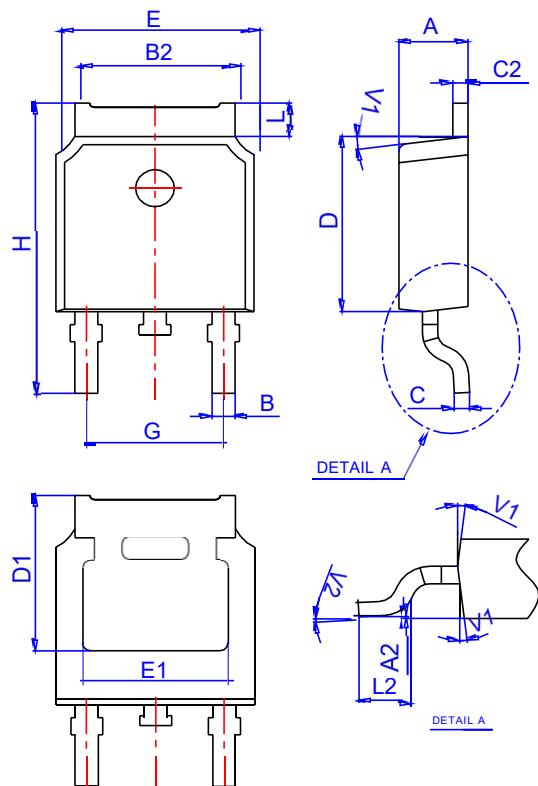


Fig.11 Unclamped Inductive Switching Waveform

Package Mechanical Data: TO-252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	TO-252-3L		2500